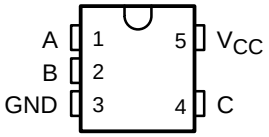
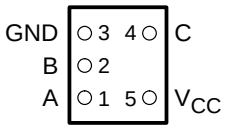
- **Available in the Texas Instruments NanoStar™ and NanoFree™ Packages**
- **Optimized for 1.8-V Operation and Is 3.6-V I/O Tolerant to Support Mixed-Mode Signal Operation**
- **Sub 1-V Operable**
- **Low Power Consumption, 10-μA Max I_{CC}**
- **High On-Off Output Voltage Ratio**
- **High Degree of Linearity**
- **High Speed – Max 0.2 ns (V_{CC} = 1.8 V, C_L = 15 pF)**
- **Low On-State Impedance – Typically ≈9 Ω (V_{CC} = 2.3 V)**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Protection Exceeds JESD 22**
  - **2000-V Human-Body Model (A114-A)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**

DBV OR DCK PACKAGE
(TOP VIEW)



YEA OR YZA PACKAGE
(BOTTOM VIEW)



description/ordering information

This single analog switch is operational at 0.8-V to 2.7-V V_{CC}, but is designed specifically for 1.65-V to 1.95-V V_{CC} operation.

The SN74AUC1G66 can handle both analog and digital signals. It permits signals with amplitudes of up to 3.6-V (peak) to be transmitted in either direction.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING‡
–40°C to 85°C	NanoStar™ WCSP (DSBGA) – YEA	Tape and reel	SN74AUC1G66YEAR	_ _ _U6_
	NanoFree™ WCSP (DSBGA) – YZA (Pb-free)	Tape and reel	SN74AUC1G66YZAR	
	SOT (SOT-23) – DBV	Tape and reel	SN74AUC1G66DBVR	U66_
	SOT (SC-70) – DCK	Tape and reel	SN74AUC1G66DCKR	U6_

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

‡ DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site.
YEA/YZA: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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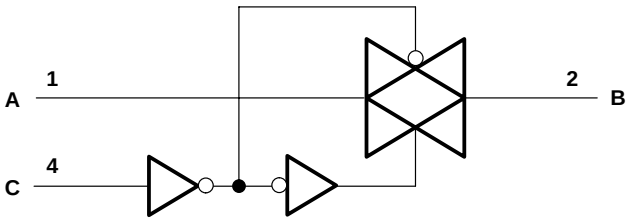
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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FUNCTION TABLE

CONTROL INPUT (C)	SWITCH
L	OFF
H	ON

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} (see Note 1) . . . . . –0.5 V to 3.6 V
Input voltage range, V_I (see Notes 1 and 2) . . . . . –0.5 V to 3.6 V
Switch I/O voltage range, $V_{I/O}$ (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Control input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
I/O port diode current, I_{IOK} ($V_{I/O}$ < 0 or $V_{I/O}$ > V_{CC}) . . . . . ±50 mA
On-state switch current, I_T ($V_{I/O}$ = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DBV package . . . . . 206°C/W
DCK package . . . . . 252°C/W
YEA/YZA package . . . . . 154°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to ground unless otherwise specified.
2. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		0.8	2.7	V
V_{IH}	High-level input voltage	V_{CC} = 0.8 V	V_{CC}		V
		V_{CC} = 1.1 V to 1.95 V	$0.65 \times V_{CC}$		
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 0.8 V		0	V
		V_{CC} = 1.1 V to 1.95 V		$0.35 \times V_{CC}$	
		V_{CC} = 2.3 V to 2.7 V		0.7	
$V_{I/O}$	I/O port voltage		0	V_{CC}	V
V_I	Control input voltage		0	3.6	V
$\Delta t/\Delta v$	Input transition rise or fall rate			20	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
r_{on}	On-state switch resistance	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$ (see Figure 1)	I_S = 4 mA	1.65 V		10	20	Ω
			I_S = 8 mA	2.3 V		9	15	
$r_{on(p)}$	Peak on resistance	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$ (see Figure 1)	I_S = 4 mA	1.65 V		32	80	Ω
			I_S = 8 mA	2.3 V		15	20	
$I_{S(off)}$	Off-state switch leakage current	$V_I = V_{CC}$ and V_O = GND, or V_I = GND and $V_O = V_{CC}$, $V_C = V_{IL}$ (see Figure 2)		2.7 V			±1	μA
							±0.1†	
$I_{S(on)}$	On-state switch leakage current	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$, V_O = Open (see Figure 3)		2.7 V			±1	μA
							±0.1†	
I_I	Control input current	$V_I = V_{CC}$ or GND		0 to 2.7 V			±5	μA
I_{CC}	Supply current	$V_I = V_{CC}$ or GND,	I_O = 0	0.8 V to 2.7 V			10	μA
C_{ic}	Control input capacitance			2.5 V		2		pF
$C_{io(off)}$	Switch input/output capacitance			2.5 V		3.5		pF
$C_{io(on)}$	Switch input/output capacitance			2.5 V		7		pF

† All typical values are at T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 0.8 V	V_{CC} = 1.2 V ± 0.1 V		V_{CC} = 1.5 V ± 0.1 V		V_{CC} = 1.8 V ± 0.15 V			V_{CC} = 2.5 V ± 0.2 V		UNIT
			TYP	MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}‡	A or B	B or A	0.9		0.3		0.2			0.2		0.1	ns
t_{en}	C	A or B	4.1	0.5	2.6	0.5	1.7	0.5	0.8	1.1	0.5	1	ns
t_{dis}	C	A or B	5	0.7	3.6	0.5	2.6	0.5	1.7	2.9	0.5	2.2	ns

‡ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

switching characteristics over recommended operating free-air temperature range, C_L = 30 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V			V_{CC} = 2.5 V ± 0.2 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}†	A or B	B or A			0.3		0.3	ns
t_{en}	C	A or B	0.5	1.4	2.3	0.8	1.4	ns
t_{dis}	C	A or B	0.5	1.7	2.9	0.5	1.5	ns

† The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

analog switch characteristics, T_A = 25°C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V_{CC}	TYP	UNIT
Frequency response† (switch ON)	A or B	B or A	C_L = 50 pF, R_L = 600 Ω, f_{in} = sine wave (see Figure 5)	0.8 V	60	MHz
				1.1 V	60	
				1.4 V	80	
				1.65 V	120	
				2.3 V	170	
			C_L = 5 pF, R_L = 50 Ω, f_{in} = sine wave (see Figure 5)	0.8 V	>500	
				1.1 V	>500	
				1.4 V	>500	
				1.65 V	>500	
				2.3 V	>500	
Crosstalk (control input to signal output)	C	A or B	C_L = 50 pF, R_L = 600 Ω, f_{in} = 1 MHz (square wave) (see Figure 6)	0.8 V	9	mV
				1.1 V	14	
				1.4 V	15	
				1.65 V	16	
				2.3 V	20	
Feed-through attenuation‡ (switch OFF)	A or B	B or A	C_L = 50 pF, R_L = 600 Ω, f_{in} = 1 MHz (sine wave) (see Figure 7)	0.8 V	–60	dB
				1.1 V	–60	
				1.4 V	–60	
				1.65 V	–60	
				2.3 V	–60	
			C_L = 5 pF, R_L = 50 Ω, f_{in} = 1 MHz (sine wave) (see Figure 7)	0.8 V	–55	
				1.1 V	–55	
				1.4 V	–55	
				1.65 V	–55	
				2.3 V	–55	
Sine-wave distortion	A or B	B or A	C_L = 50 pF, R_L = 10 kΩ, f_{in} = 1 kHz (sine wave) (see Figure 8)	0.8 V	7.5	%
				1.1 V	0.16	
				1.4 V	0.04	
				1.65 V	0.03	
				2.3 V	0.02	
	A or B	B or A	C_L = 50 pF, R_L = 10 kΩ, f_{in} = 10 kHz (sine wave) (see Figure 8)	0.8 V	4.2	
				1.1 V	0.2	
				1.4 V	0.03	
				1.65 V	0.02	
				2.3 V	0.02	

† Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads –3 dB.
‡ Adjust f_{in} voltage to obtain 0 dBm at input.

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC} = 0.8 V	V_{CC} = 1.2 V	V_{CC} = 1.5 V	V_{CC} = 1.8 V	V_{CC} = 2.5 V	UNIT
			TYP	TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	f = 10 MHz	3	3	3	3	3	pF

PARAMETER MEASUREMENT INFORMATION

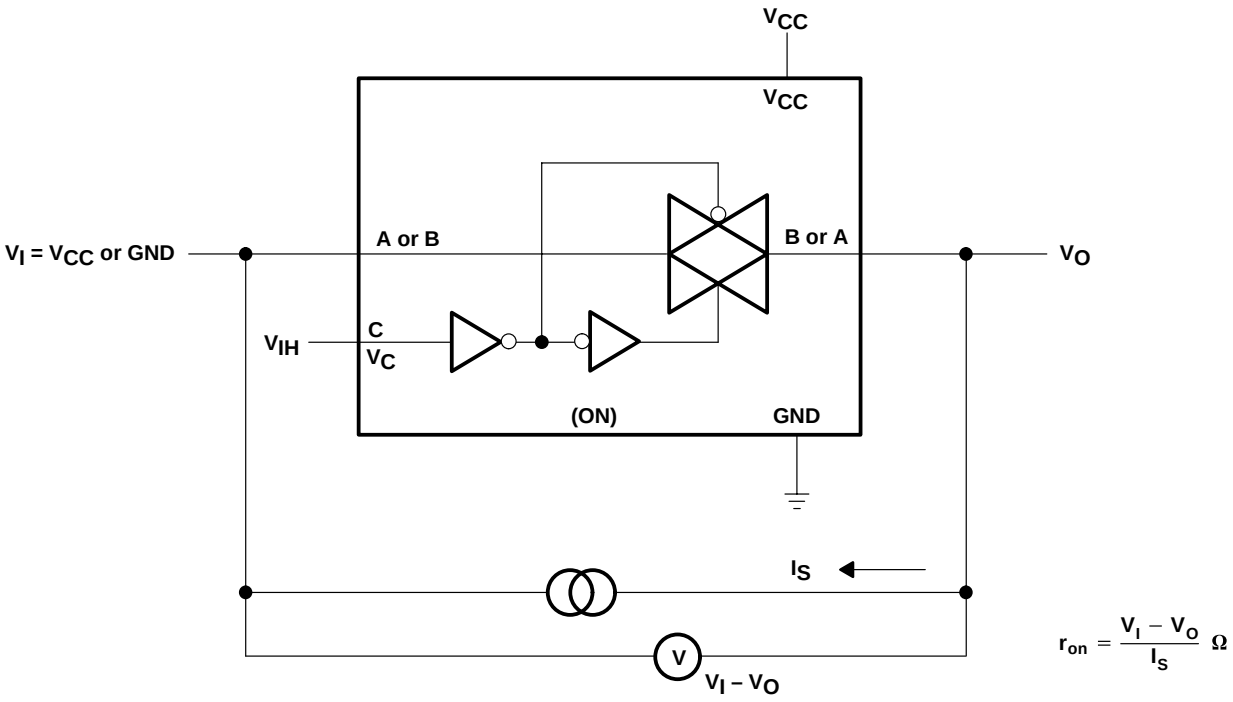


Figure 1. On-State Resistance Test Circuit

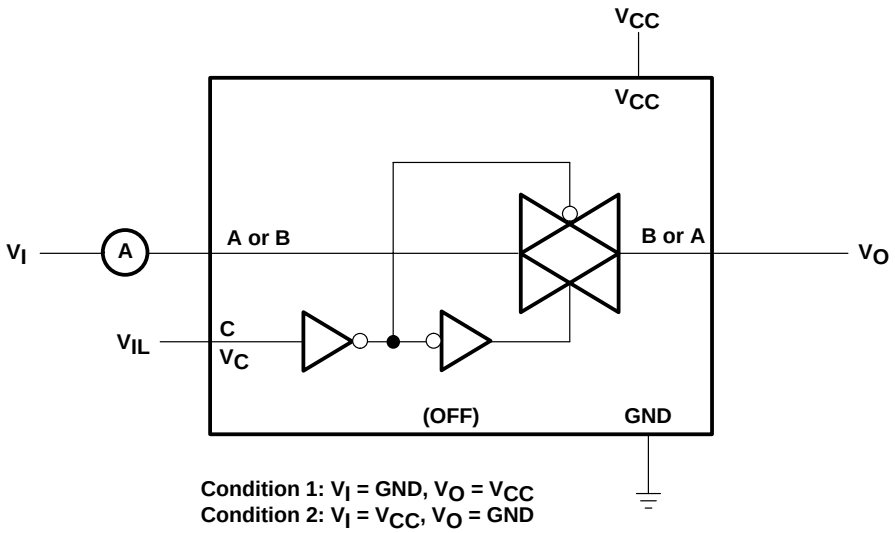


Figure 2. Off-State Switch Leakage-Current Test Circuit

PARAMETER MEASUREMENT INFORMATION

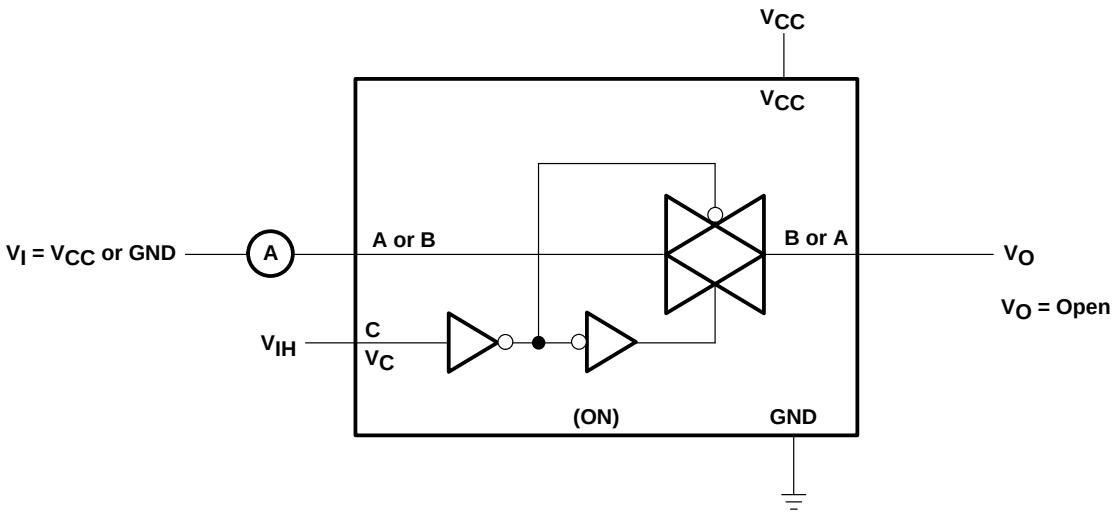
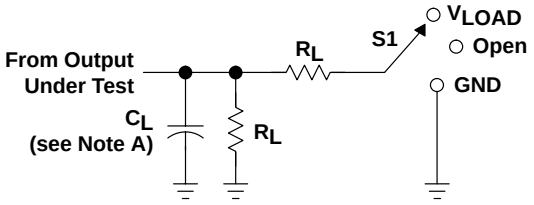


Figure 3. On-State Leakage-Current Test Circuit

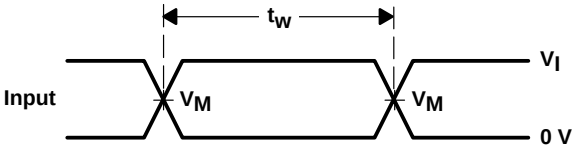
PARAMETER MEASUREMENT INFORMATION



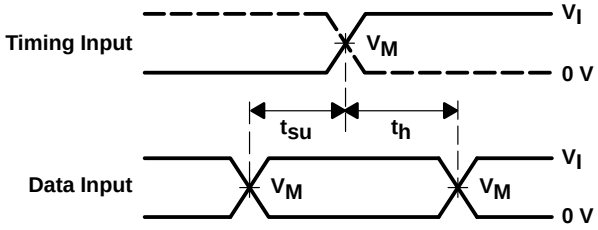
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

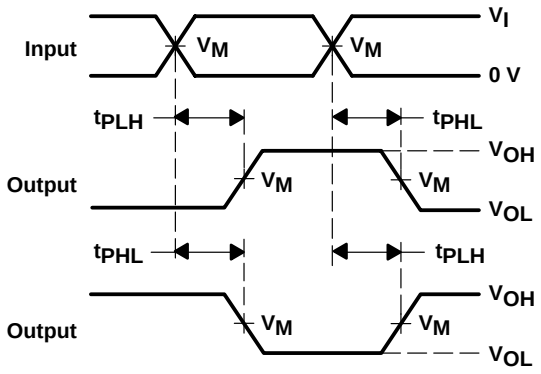
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
0.8 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 kΩ	0.1 V
1.2 V ± 0.1 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 kΩ	0.1 V
1.5 V ± 0.1 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 kΩ	0.1 V
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 kΩ	0.15 V
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V



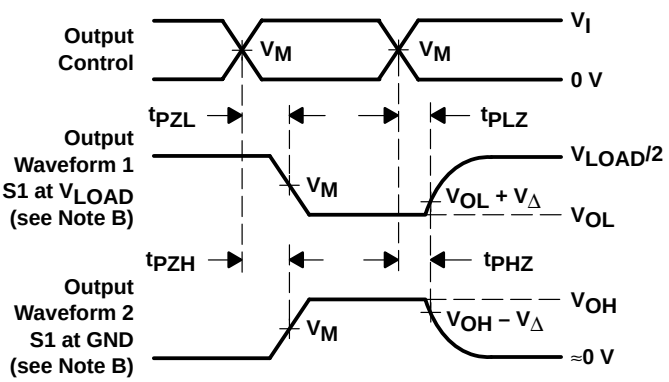
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, slew rate ≥ 1 V/ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

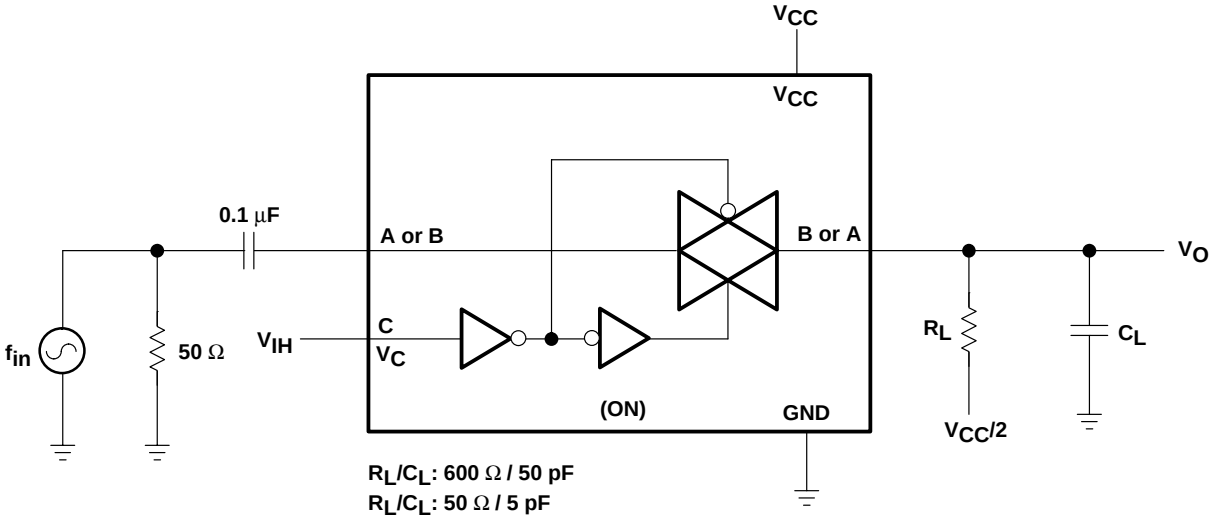


Figure 5. Frequency Response (Switch ON)

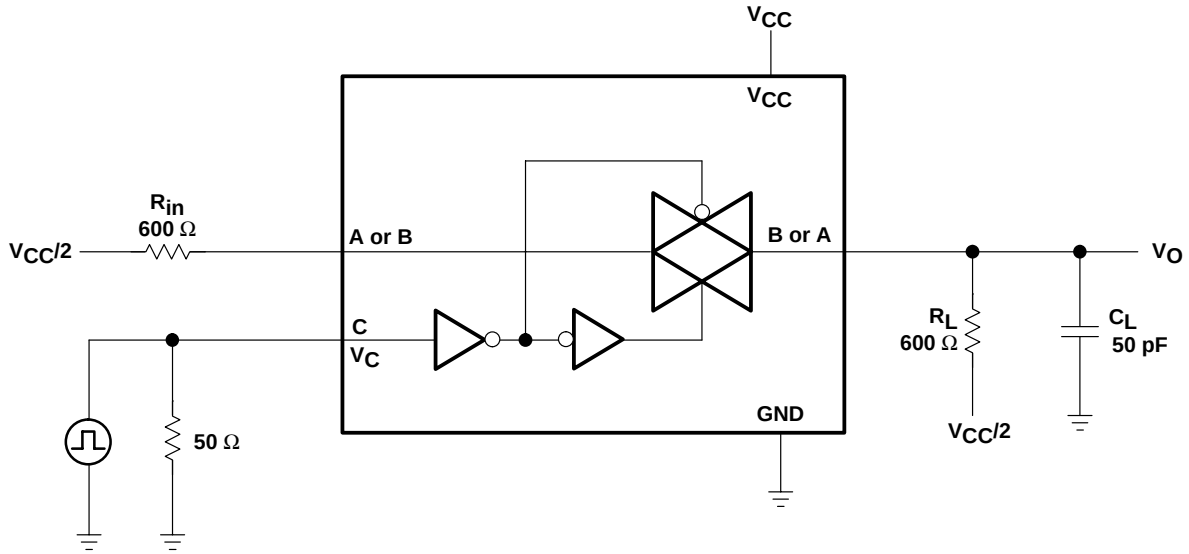


Figure 6. Crosstalk (Control Input – Switch Output)

PARAMETER MEASUREMENT INFORMATION

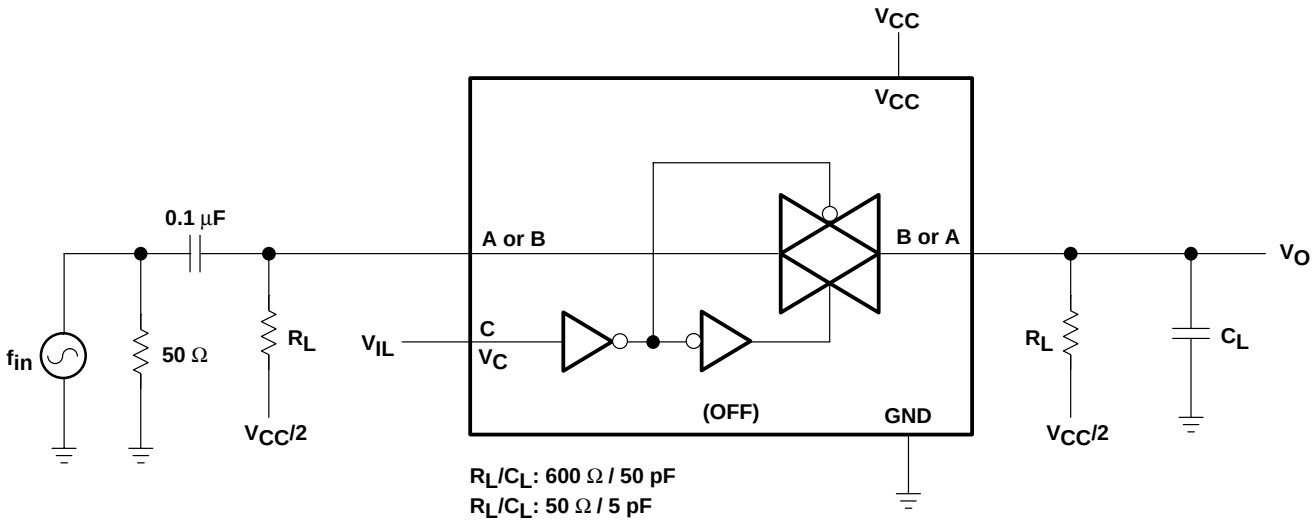


Figure 7. Feed Through, Switch Off

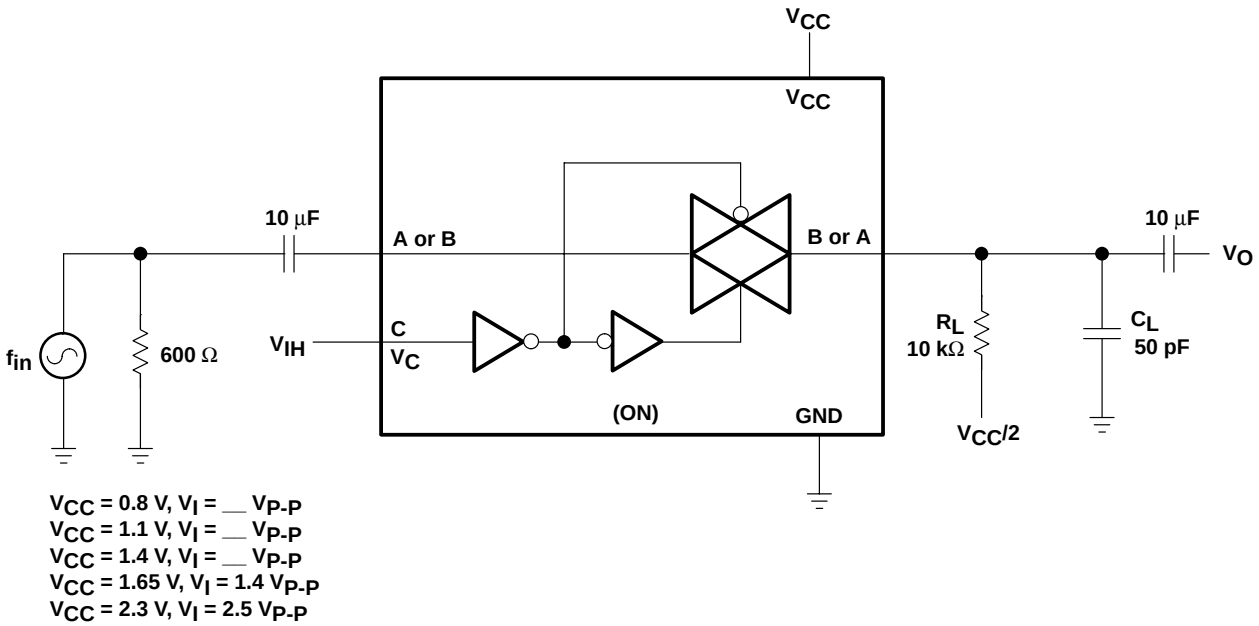
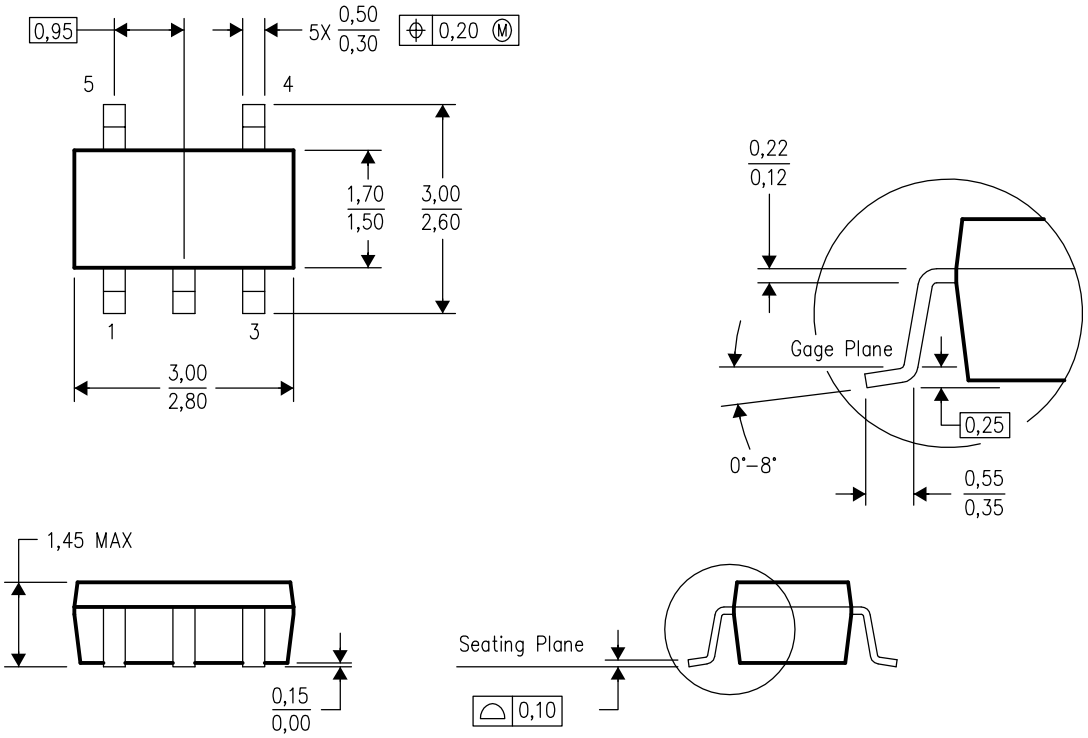


Figure 8. Sine-Wave Distortion

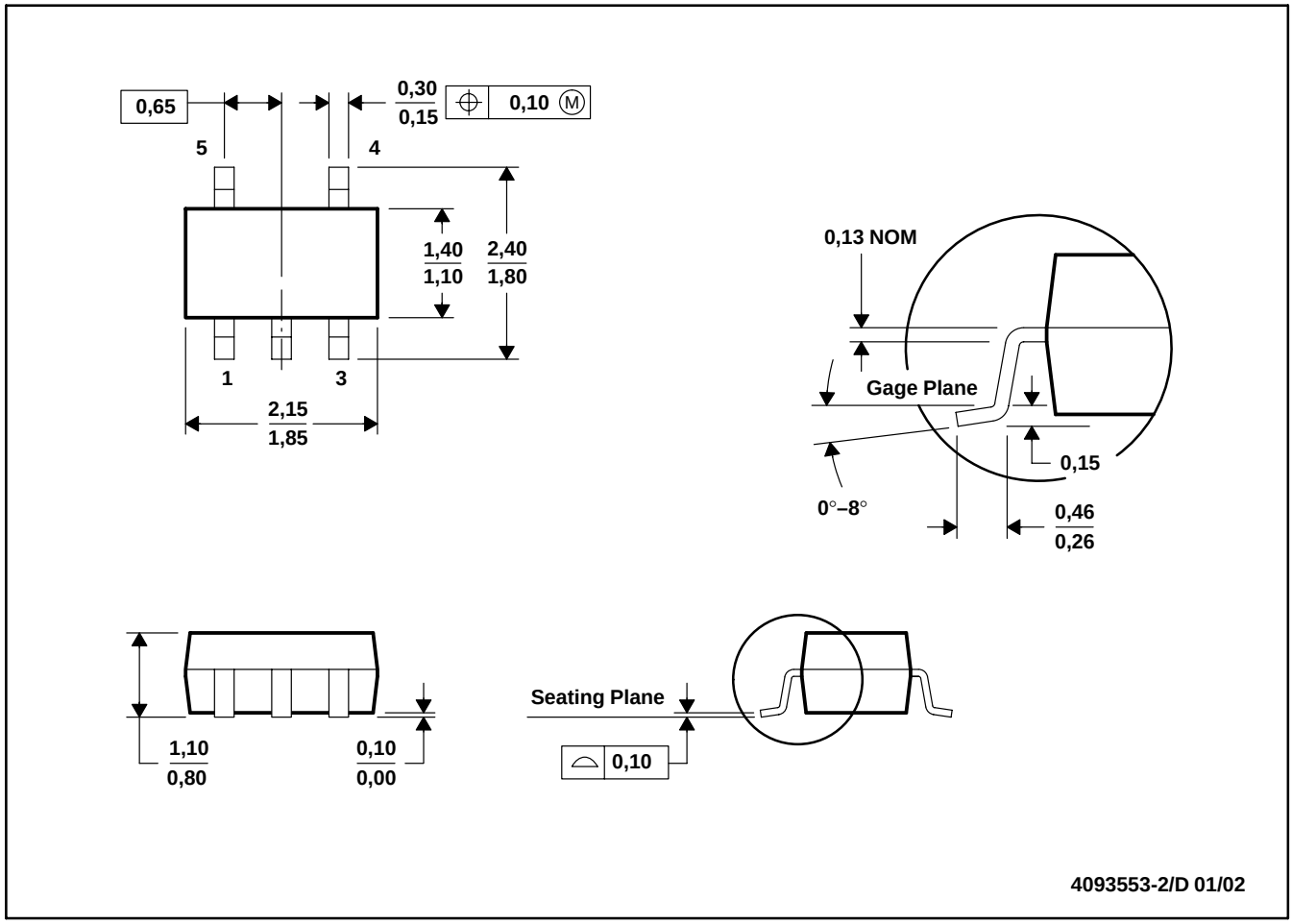
DBV (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4073253–4/H 10/2003

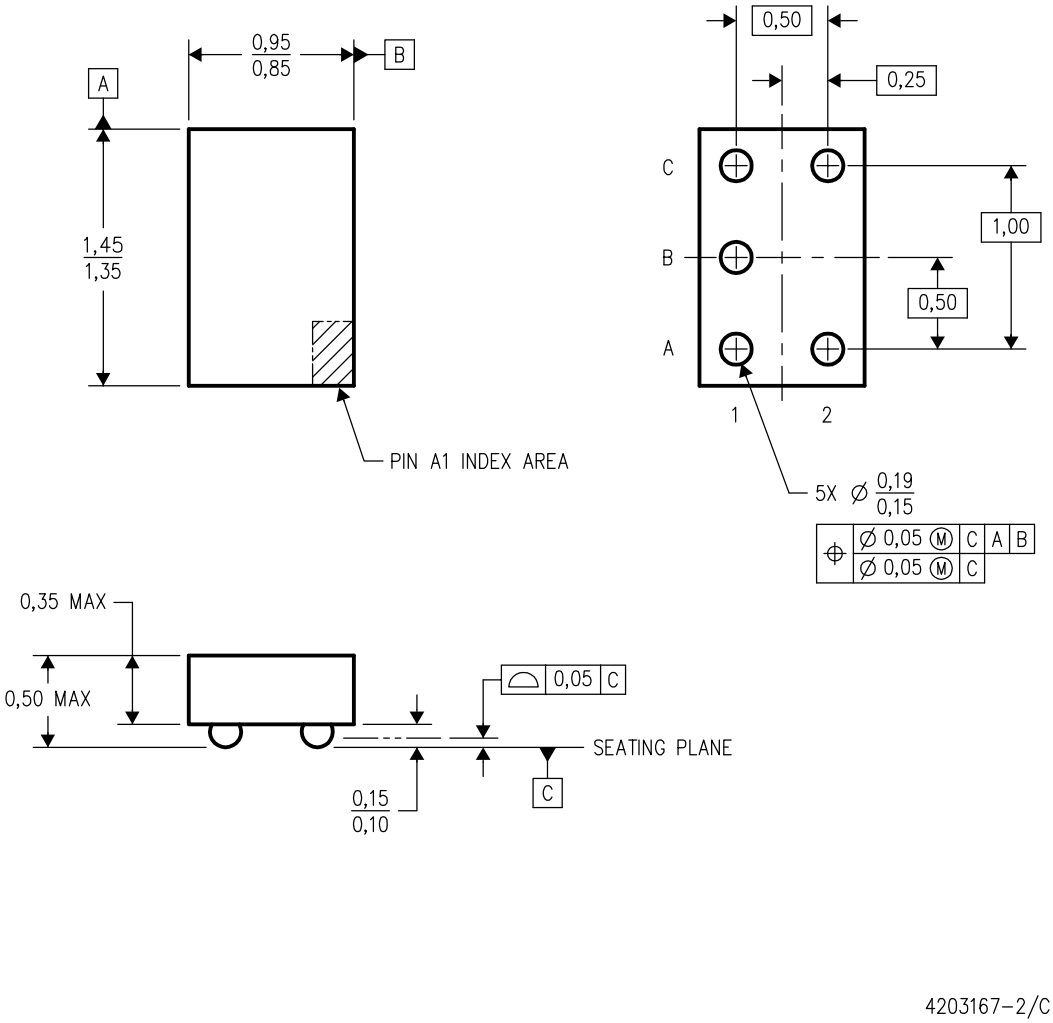
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion.
D. Falls within JEDEC MO–178 Variation AA.

DCK (R-PDSO-G5) **PLASTIC SMALL-OUTLINE PACKAGE**



NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion.
D. Falls within JEDEC MO-203

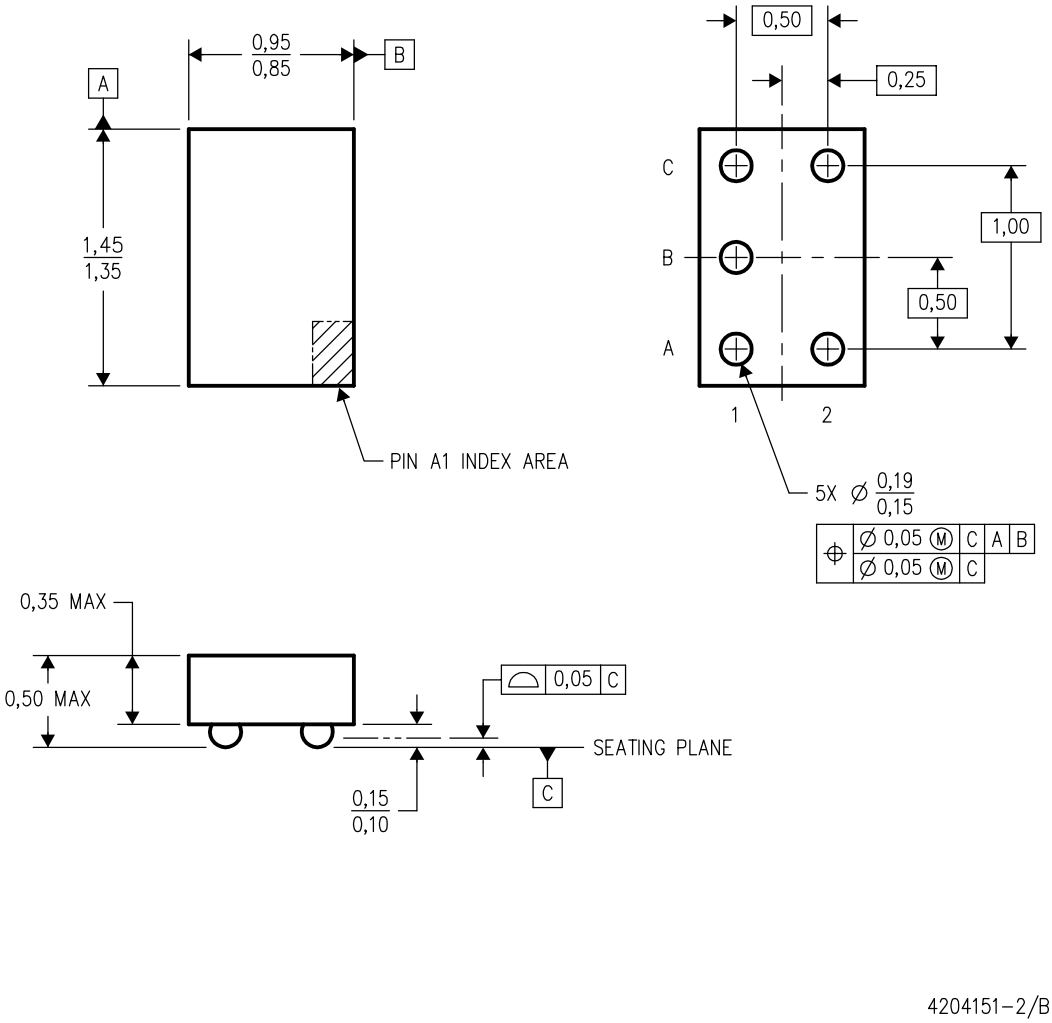
YEA (R–XBGA–N5) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. NanoStar™ package configuration.
D. Package complies to JEDEC MO–211 variation EA.
E. This package is tin–lead (SnPb). Refer to the 5 YZA package (drawing 4204151) for lead–free.

NanoStar is a trademark of Texas Instruments.

YZA (R–XBGA–N5) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.
D. Package complies to JEDEC MO–211 variation EA.
E. This package is lead–free. Refer to the 5 YEA package (drawing 4203167) for tin–lead (SnPb).

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